TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

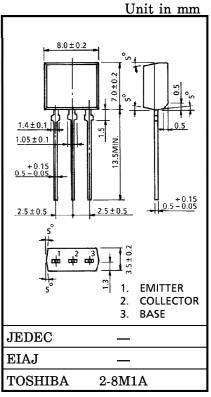
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POWER AMPLIFIER APPLICATIONS

- High DC Current Gain
 - : $h_{FE(1)} = 300 \sim 1000$
- Low Collector Saturation Voltage
 - : $V_{CE (sat)} = -0.5V (Typ.)$
- Complementary to 2SD2462

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage	v_{CBO}	-60	V		
Collector-Emitter Voltage		v_{CEO}	-60	V	
Emitter-Base Voltage		$V_{ m EBO}$	- 7	V	
Collector Current	DC	$I_{\mathbf{C}}$	-3	A	
	Pulse	I_{CP}	-6		
Base Current	$I_{\mathbf{B}}$	-0.6	A		
Collector Power Dissipation		PC	1.3	W	
Junction Temperature		T_{j}	150	$^{\circ}\mathrm{C}$	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$	

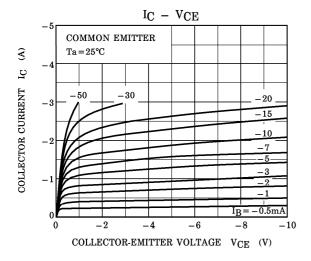


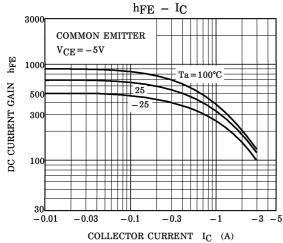
Weight: 0.55g (Typ.)

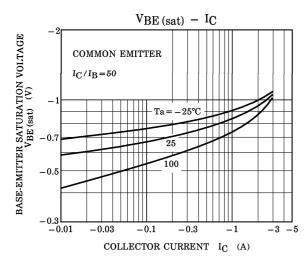
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

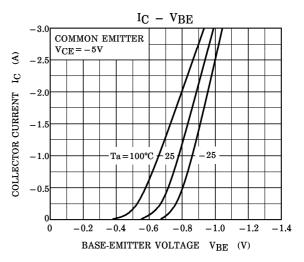
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = -60V, I_{E} = 0$	_	_	-100	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -7V, I_C = 0$	_	_	-100	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{C} = -50 \text{mA}, I_{B} = 0$	-60	_	_	V
DC Current Gain	h _{FE (1)}	$V_{CE} = -5V, I_{C} = -0.5A$	300	_	1000	
	h _{FE} (2)	$V_{CE} = -5V, I_{C} = -1.5A$	350		_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = -2A, I_B = -20mA$	ı	-0.5	-1.5	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -5V, I_{C} = -0.5A$	_	-0.7	-1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$	_	60	_	pF

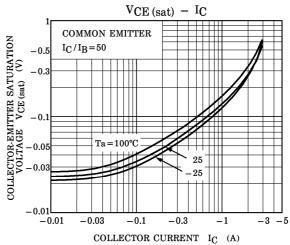
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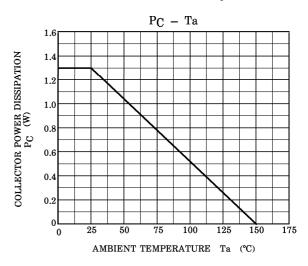




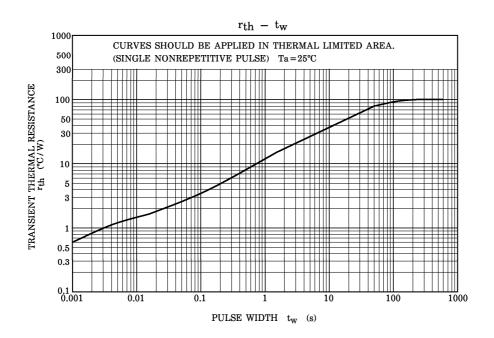


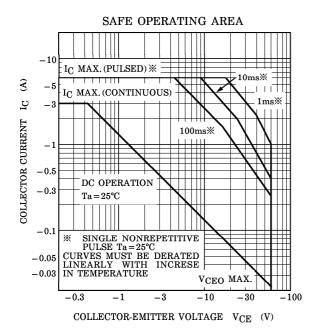






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